

**INFORMATION DISCLOSURE
STATEMENT**
 Atty Docket:
 Serial No.:
 Applicant:
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 Group: 283

SE1645PD (50042)

~~Not Yet Assigned~~

ZENG

Herewith

09/844,347
04/27/01
 JCS29 U.S. PRO
 09/844347

04/27/01

U.S. PATENT DOCUMENTS

Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
<i>[Signature]</i>	AA	5,567,634	10/22/96	Hébert et al.	437	41	
<i>[Signature]</i>	AB	5,665,619	9/9/97	Kwan et al.	438	270	
<i>[Signature]</i>	AC	6,121,089	9/19/00	Zeng et al.	438	268	
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub Class	Translation
	AM						
	AN						
	AO						
	AP						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

<i>[Signature]</i>	AQ	Zeng, <i>An Improved Power MOSFET Using a Novel Split Well Structure</i> , Harris Corporation, Semiconductor Section, Technical Publication, 4 pages					
<i>[Signature]</i>	AR	Zeng et al., <i>An Ultra Dense Trench-Gated Power MOSFET Technology Using a Self-Aligned Process</i> , Intersil Corporation, Technical Publication, 4 pages					
	AS						

EXAMINER:

[Signature]

DATE CONSIDERED:

2/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.